

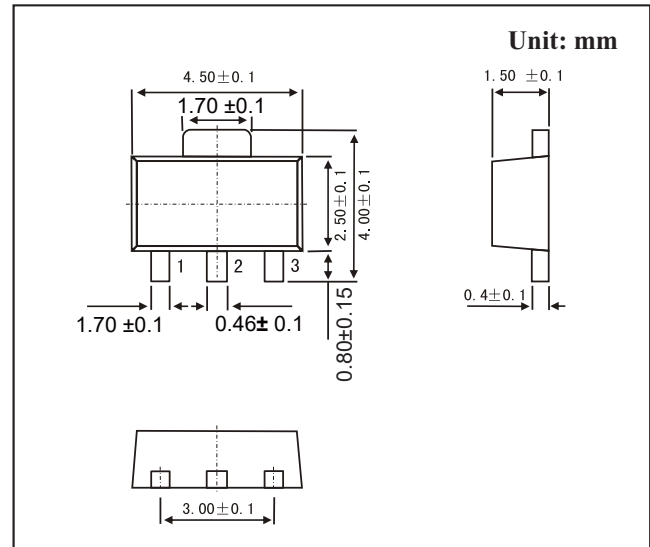
SOT-89 Plastic-Encapsulate Transistors

Features

- Epitaxial planar die construction
- Complementary to PXT2907A
- NPN Transistors

MECHANICAL DATA

- Case style: SOT-89 molded plastic
- Mounting position: any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	75	V
Collector - Emitter Voltage	V_{CE0}	40	
Emitter - Base Voltage	V_{EB0}	6	
Collector Current - Continuous	I_C	600	mA
Collector Power Dissipation	P_C	500	mW
Junction Temperature	T_J	150	°C
Storage Temperature Range	T_{stg}	-55 to 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_C = 100 \mu A, I_E = 0$	75			V
Collector- emitter breakdown voltage	V_{CE0}	$I_C = 10 mA, I_B = 0$	40			
Emitter - base breakdown voltage	V_{EB0}	$I_E = 100 \mu A, I_C = 0$	6			
Collector-base cut-off current	I_{CBO}	$V_{CB} = 60 V, I_E = 0$			50	nA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5 V, I_C = 0$			50	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500 mA, I_B = 50 mA$			1	V
		$I_C = 500 mA, I_B = 15 mA$			0.3	
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = 500 mA, I_B = 50 mA$			2	
		$I_C = 500 mA, I_B = 15 mA$		0.6	1.2	
	$h_{FE(1)}$	$V_{CE} = 10 V, I_C = 0.1 mA$	50			
	$h_{FE(2)}$	$V_{CE} = 10 V, I_C = 10 mA$	75			
	$h_{FE(3)}$	$V_{CE} = 10 V, I_C = 150 mA$	100		300	
	$h_{FE(4)}$	$V_{CE} = 1 V, I_C = 150 mA$	50			
	$h_{FE(5)}$	$V_{CE} = 10 V, I_C = 500 mA$	40			
Delay time	t_d	$V_{CC} = 30 V, I_C = 150 mA$			10	ns
Rise time	t_r	$V_{BE(off)} = 0.5 V, I_{B1} = 15 mA$			25	
Storage time	t_s	$V_{CC} = 30 V, I_C = 150 mA$			225	
Fall time	t_f	$I_{B1} = - I_{B2} = 15 mA$			60	
Collector output capacitance	C_{ob}	$V_{CB} = 10 V, I_E = 0, f = 1 MHz$			8	pF
Transition frequency	f_T	$V_{CE} = 10 V, I_C = 20 mA, f = 100 MHz$	300			MHz

■ Marking

Marking	*1P
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RATINGS AND CHARACTERISTIC CURVES

■ Typical Characteristics

